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FORM PTO 1449 (modified)			ATTY DOCKET NO. 00862,022541	APPLICATION NO. 10/091,461		
U.S. DEPARTMENT OF COMMERCE PATENT END TRADEMARK OFFICE			APPLICANT MASATAKA ITO			
LIST OF REFERENCES ATTED BY APPLICANT(S) (Use several sites if necessary) MAY 1 5 2002 H			FILING DATE March 7, 2002	GROUP 2812		
MAI	\$	U.S. PATENT DOCUMENTS				
EXAMINER TA	DE NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE # APPROPRIATE
SDI	5,869,387	02/09/1999	Sato et al.	438	459	03/13/1995
SDF	6,171,982	01/09/2001	Sato	438	795	12/22/1998
FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
Id2	05-152230	06/18/1993	Japan			Abstract
SDF	05-217821	08/27/1993	Japan			Abstract
SIX	11-265893	09/28/1999	Japan			Abstract
OTHER DOCUMENT(S) (Including Author, Title, Date, Perlinent Pages, Etc.)						
ZII	"Nano-Defects In Commercial Bonded SOI And SIMOX", D.K. Sadana et al., 1994 IEEE International SOI Conference Proceedings, October 1994, pp. 111-112.					
SDI	"Extremely Low Si Etching (<1nm) During Hydrogen Annealing of Silicon-on-Insulator", N. Sato et al., Extended Abstracts of the 1998 International Conference on Solid State Devices And Materials, Hiroshima, 1998, pp.298-299.					
SDF	"Suppression of Si Etching During Hydrogen Annealing of Silicon-on-Insulator" N. Sato et al., 1998 IEEE International SOI Conference Proceedings, October 1998, pp. 17-18.					
SPI	"Hydrogen Annealing Treatment Used To Obtain High Quality SOI Surfaces" H. Moriceau et al., 1998 IEEE International SOI Conference Proceedings, October 1998, pp. 37-38.					
507	"Defect Reduction Of Bonded SOI Wafers By Post Anneal Process In H, Ambient", N. Tate et al., 1998 IEEE International SOI Conference Proceedings, October 1988, pp. 141-142					
EXAMINER Standth Space DATE CONSIDERED 11/7/03						

*EXAMINER: Initial If reference considered, whether or not distion is in conformance with MPEP 609, Draw line through distion if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form #62 CA_MAIN 41518 v 1 Sheet_1_ of _1_